

Automotive-grade N-channel 200 V, 0.10 Ω typ., 18 A STripFET™ Power MOSFET in a DPAK package

Datasheet - production data

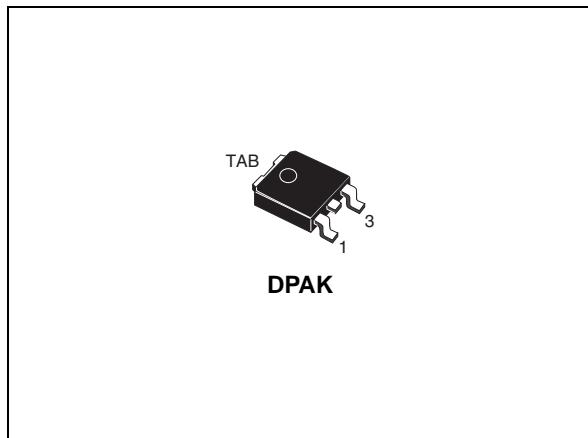
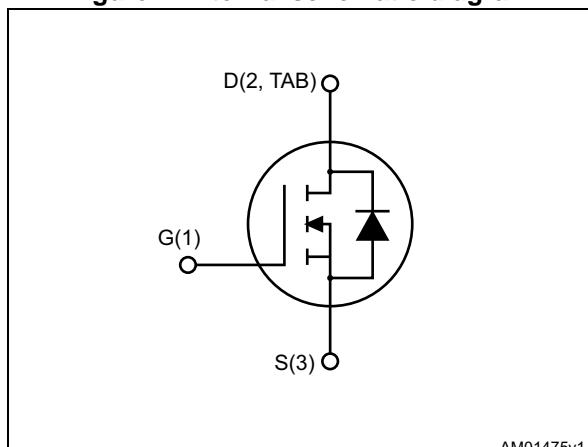


Figure 1. Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)} max	I _D	P _{TOT}
STD25NF20	200 V	0.125 Ω	18 A	110 W

- Designed for automotive applications and AEC-Q101 qualified
- Extremely low gate charge
- Exceptional dv/dt capability
- Low gate input resistance
- 100% avalanche tested

Applications

- Switching applications

Description

This N-channel enhancement mode Power MOSFET benefits from the latest refinement of STMicroelectronics' unique "single feature size" strip-based process, which decreases the critical alignment steps to offer exceptional manufacturing reproducibility. The result is a transistor with extremely high packing density for low on-resistance, rugged avalanche characteristics and low gate charge.

Table 1. Device summary

Order code	Marking	Package	Packing
STD25NF20	25NF20	DPAK	Tape and reel

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
2.1	Electrical characteristics (curves)	6
3	Test circuits	8
4	Package information	9
4.1	DPAK (TO-252) package information	10
4.2	Packing information	13
5	Revision history	15

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	200	V
V_{GS}	Gate-source voltage	± 20	
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	18	A
	Drain current (continuous) at $T_C = 100^\circ\text{C}$	11	
$I_{DM}^{(1)}$	Drain current (pulsed)	72	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	110	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
T_{stg}	Storage temperature	-55 to 175	$^\circ\text{C}$
T_j	Operating junction temperature		

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 18 \text{ A}$, $di/dt \leq 200 \text{ A}/\mu\text{s}$; $V_{DS \text{ peak}} < V_{(\text{BR})DSS}$, $V_{DD} = 80\% V_{(\text{BR})DSS}$.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	1.38	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}$	Thermal resistance junction-pcb	50 ⁽¹⁾	

1. When mounted on 1 inch² FR-4, 2 Oz copper board

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	18	A
E_{AS}	Single pulse avalanche energy (starting $T_j=25^\circ\text{C}$, $I_D=I_{AR}$; $V_{DD}=50 \text{ V}$)	110	mJ

2 Electrical characteristics

($T_C = 25^\circ\text{C}$ unless otherwise specified)

Table 5. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(\text{BR})\text{DSS}}$	Drain-source breakdown voltage	$I_D = 1 \text{ mA}, V_{GS} = 0$	200			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 200 \text{ V}$			1	μA
		$V_{DS} = 200 \text{ V}, T_C = 125^\circ\text{C}$			50	μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20 \text{ V}$			± 100	nA
$V_{GS(\text{th})}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	2	3	4	V
$R_{DS(\text{on})}$	Static drain-source on-resistance	$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$		0.10	0.125	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}, V_{GS} = 0$	-	940		pF
C_{oss}	Output capacitance		-	197		pF
C_{rss}	Reverse transfer capacitance		-	30		pF
Q_g	Total gate charge	$V_{DD} = 160 \text{ V}, I_D = 20 \text{ A}, V_{GS} = 10 \text{ V}$ (see Figure 13)	-	28	39	nC
Q_{gs}	Gate-source charge		-	5.6		nC
Q_{gd}	Gate-drain charge		-	14.5		nC

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_d(\text{on})$	Turn-on delay time	$V_{DD} = 100 \text{ V}, I_D = 10 \text{ A}, R_G = 4.7 \Omega, V_{GS} = 10 \text{ V}$ (see Figure 14 and Figure 17)	-	15	-	ns
$t_r(v)$	Voltage rise time		-	30	-	ns
$t_d(\text{off})$	Turn-off-delay time		-	40	-	ns
$t_f(i)$	Fall time		-	10	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		18	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		72	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 20 \text{ A}, V_{GS} = 0$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 20 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 50 \text{ V}$ (see Figure 17)	-	155		ns
Q_{rr}	Reverse recovery charge		-	775		nC
I_{RRM}	Reverse recovery current		-	10		A
t_{rr}	Reverse recovery time	$I_{SD} = 20 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 50 \text{ V}, T_j = 150 \text{ }^\circ\text{C}$ (see Figure 17)	-	183		ns
Q_{rr}	Reverse recovery charge		-	1061		nC
I_{RRM}	Reverse recovery current		-	11.6		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

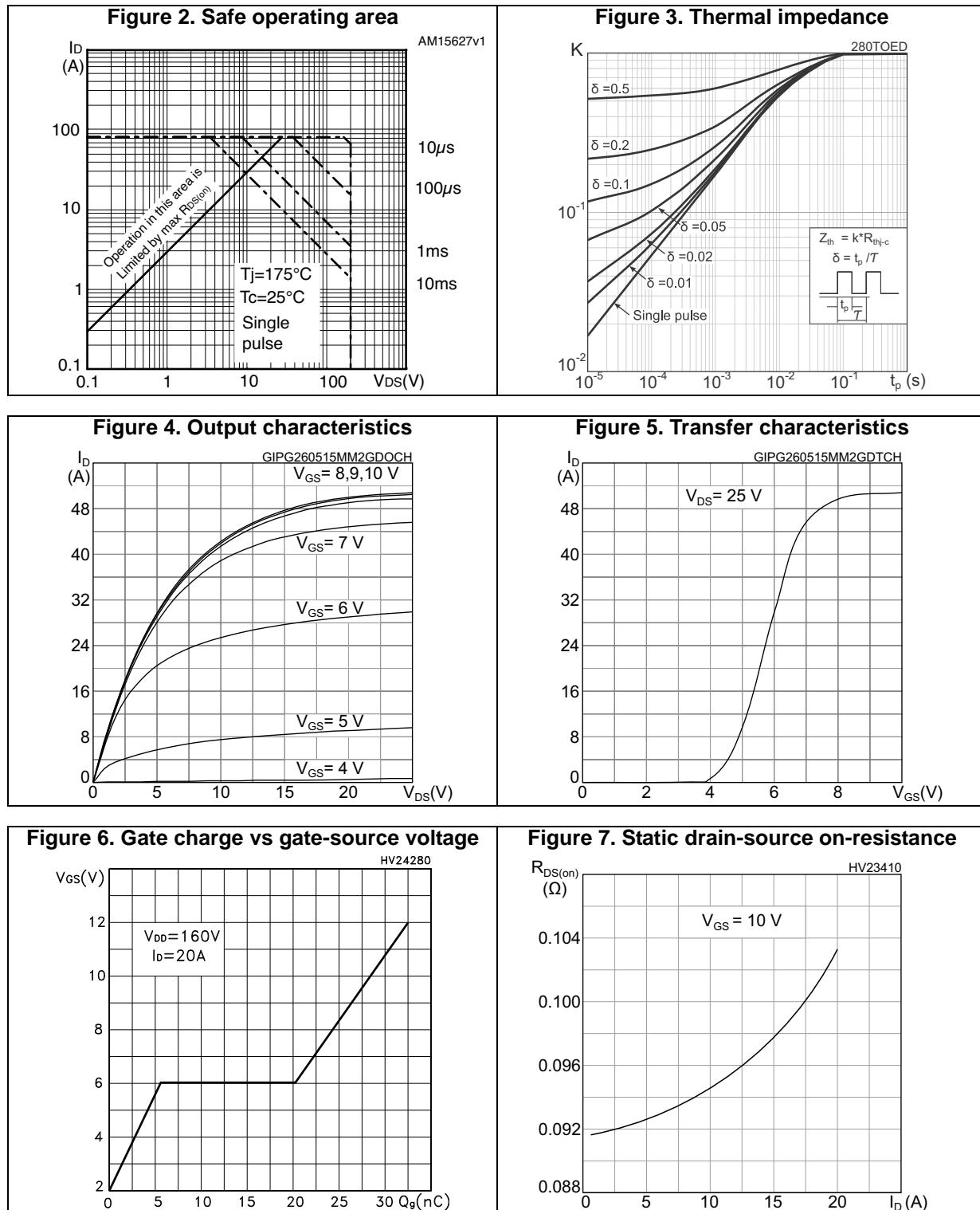
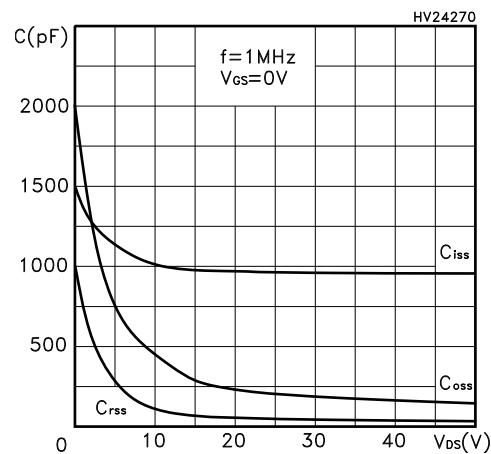
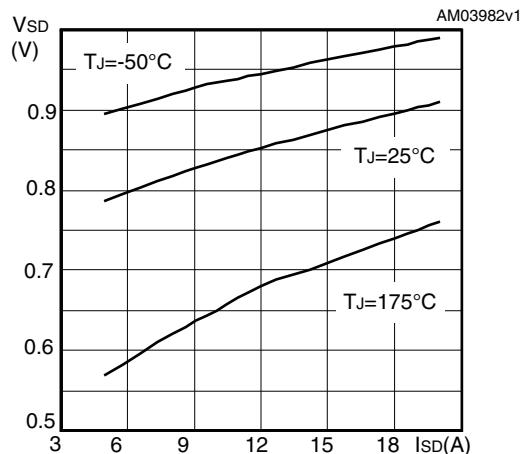
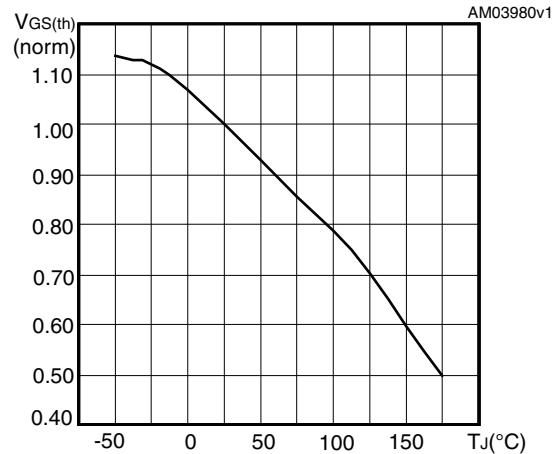
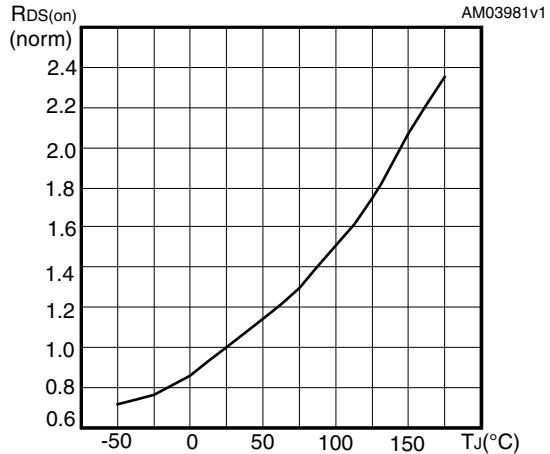
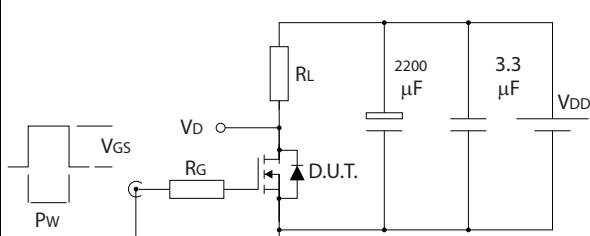


Figure 8. Capacitance variations**Figure 9. Source-drain diode forward characteristics****Figure 10. Normalized gate threshold voltage vs temperature****Figure 11. Normalized on-resistance vs temperature**

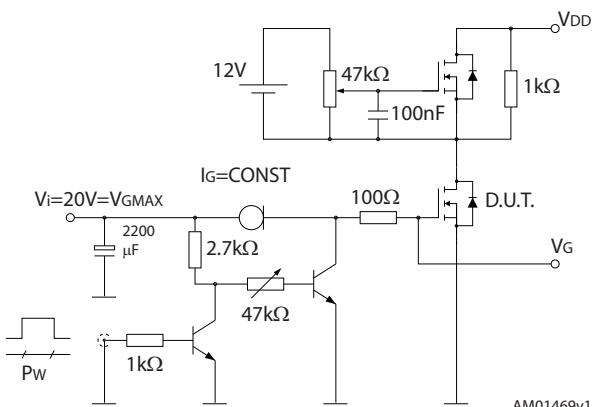
3 Test circuits

Figure 12. Switching times test circuit for resistive load



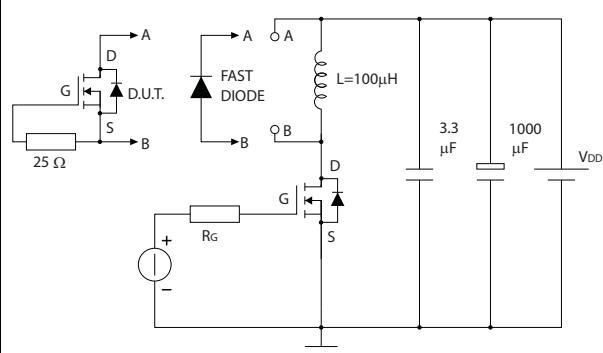
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Figure 13. Gate charge test circuit



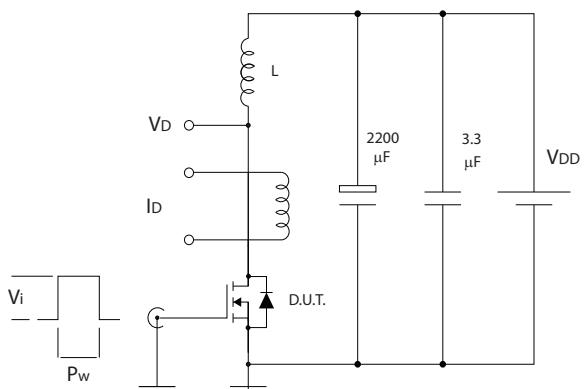
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Figure 14. Test circuit for inductive load switching and diode recovery times



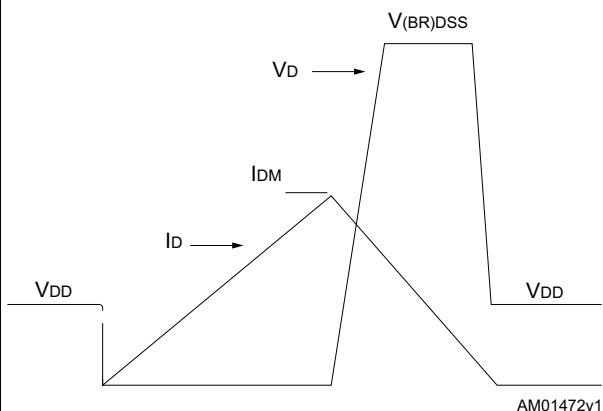
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Figure 15. Unclamped inductive load test circuit



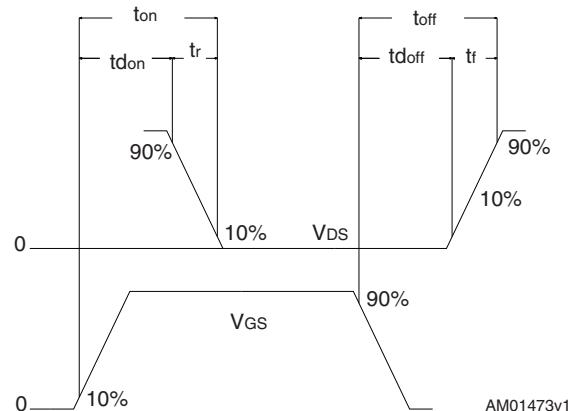
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Figure 16. Unclamped inductive waveform



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Figure 17. Switching time waveform



AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com.
ECOPACK® is an ST trademark.

4.1 DPAK (TO-252) package information

Figure 18. DPAK (TO-252) type A2 package outline

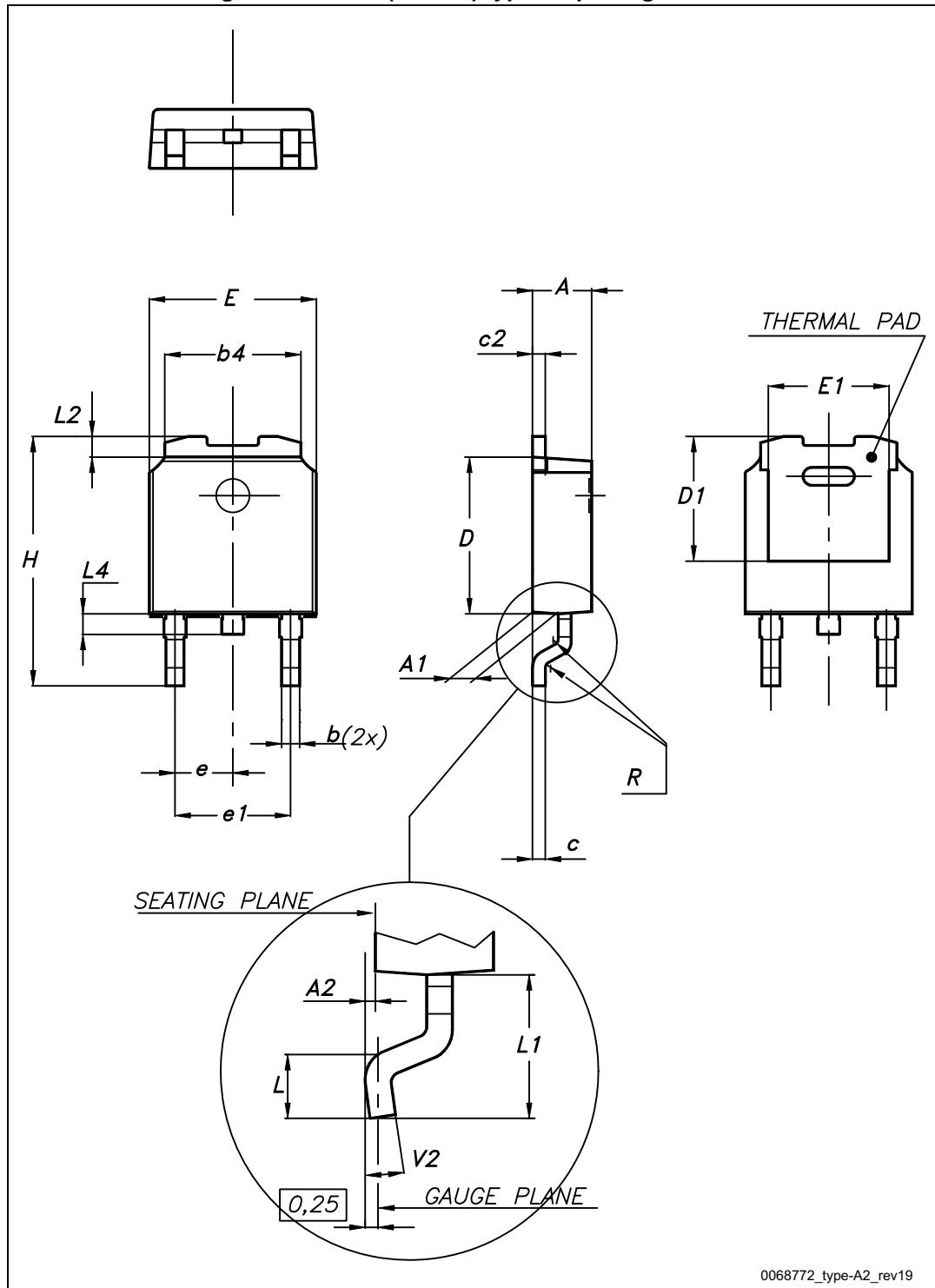
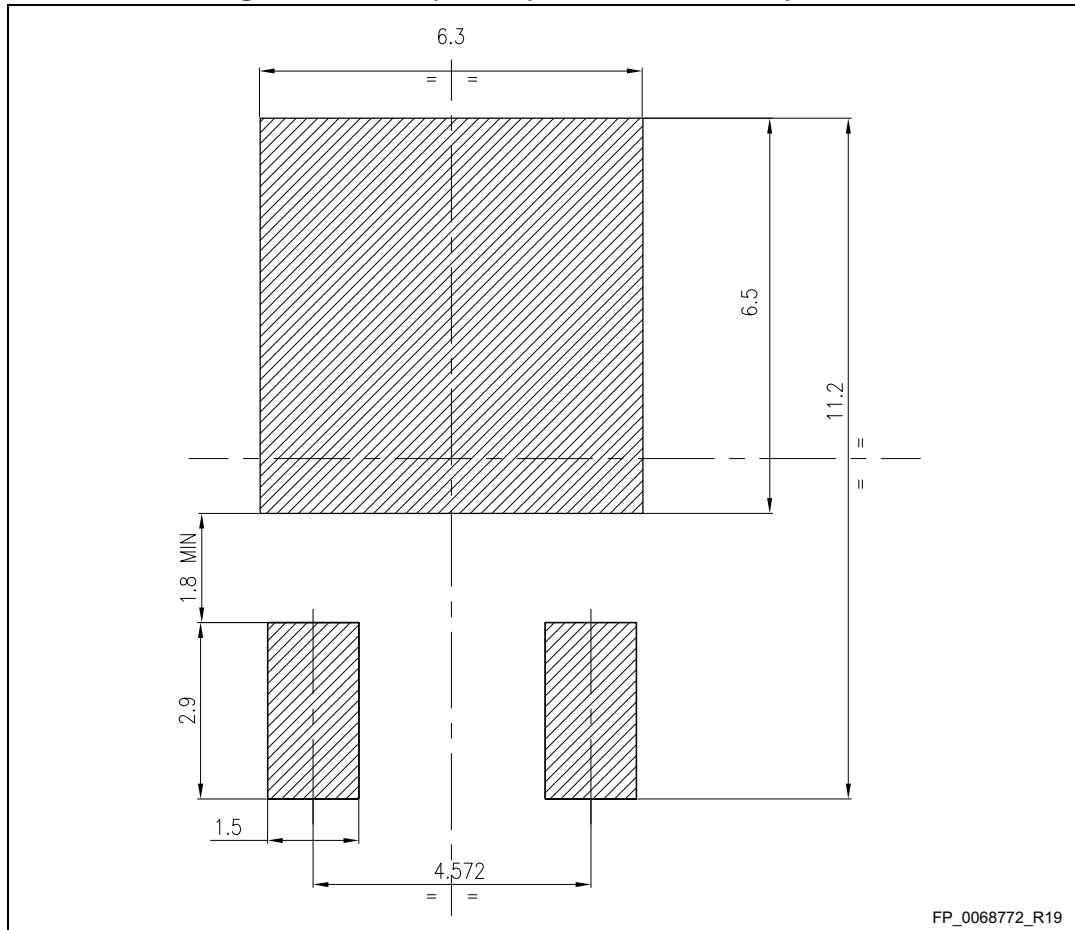


Table 9. DPAK (TO-252) type A2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.16	2.28	2.40
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 19. DPAK (TO-252) recommended footprint (a)

a. All dimensions are in millimeters

4.2 Packing information

Figure 20. Tape outline for DPAK (TO-252)

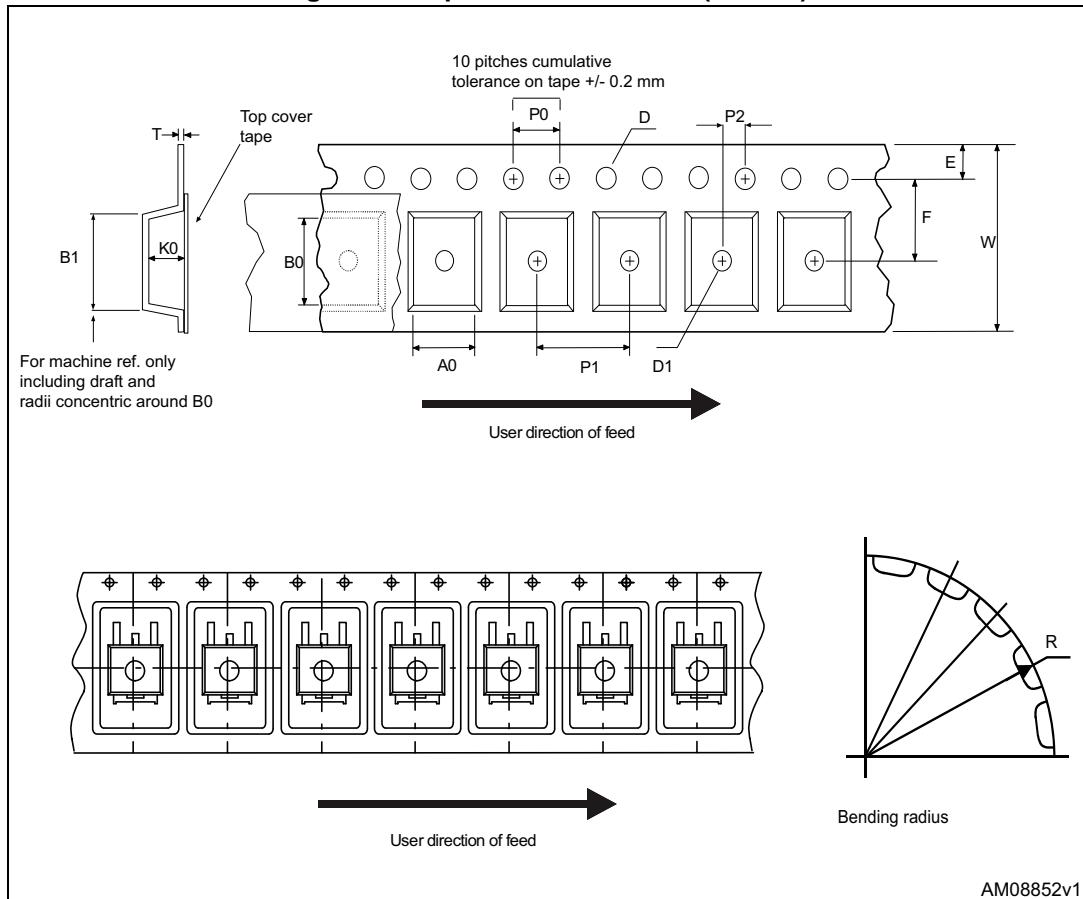


Figure 21. Reel outline for DPAK (TO-252)

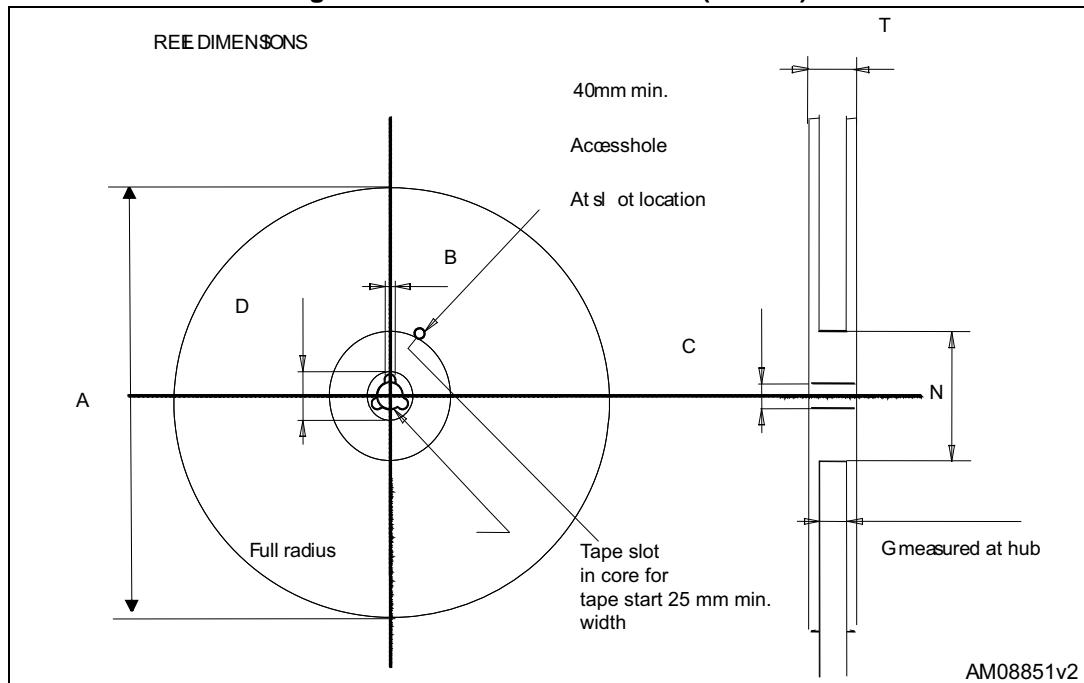


Table 10. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1		Base qty.	2500
P1	7.9	8.1		Bulk qty.	2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

5 Revision history

Table 11. Document revision history

Date	Revision	Changes
12-Mar-2013	1	First release.
03-Sep-2013	2	<ul style="list-style-type: none">- Modified: title and <i>Features</i> in cover page- Modified: <i>Figure 12, 13, 14</i> and <i>15</i>- Minor text changes
27-May-2015	3	<p>Text and formatting changes throughout document.</p> <p>In <i>Section 1: Electrical ratings</i>:</p> <ul style="list-style-type: none">- updated <i>Table 2</i> and <i>Table 3</i> <p>In <i>Section 1: Electrical ratings</i>:</p> <ul style="list-style-type: none">- updated <i>Table 8</i> <p>In <i>Section 2.1: Electrical characteristics (curves)</i>:</p> <ul style="list-style-type: none">- updated <i>Figure 4</i> and <i>Figure 5</i> <p>Updated <i>Section 4: Package information</i></p>

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